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FAX COVER SHEET

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DATE:

FROM: David Denker COMPANY: Texas Instruments Incorporated PHONE NUMBER: (972) 917-4388 FAX NUMBER: (972) 917-4418	TO: Examiner: B. Souw U.S. Patent & Trademark Office Group: 2814 PHONE NUMBER: 703-305-1481 3303 FAX NUMBER: 703-308-7722

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Re: Appl.#: 09/116,138

Atty Docket: TI-24953

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DEC 04 2000

Response Under 37 C.F.R. § 1.116 - Expedited Procedure

TECHNOLOGY CENTER 2800

Examining Group 2814

Response Under 37 C.F.R. § 1.116 - Expedited Procedure
Examining Group 2814

IN THE UNITED STATES PATENT AND TRADEMARK OFFICEIn re the application of: Anthony *et al.*

Serial No.: 09/116,138

Filed: 07/15/98

For: High Permittivity Silicate Gate Dielectric

Docket:

TI-24953

Examiner:

B. Souw

Art Unit:

2814

FAX COPY RECEIVED**DEC 04 2000****AMENDMENT PURSUANT TO 37 C.F.R. § 1.116**

TECHNOLOGY CENTER 2800

November 29, 2000

Ass't Commissioner for Patents
Washington, DC 20231

<p>FACSIMILE CERTIFICATE</p> <p>I hereby certify that this correspondence is being transmitted by Facsimile to the Patent and Trademark Office in accordance with 37 C.F.R. § 1.6d on</p> <p><u>December 4</u>, 2000.</p> <p><u>Tina Rendon</u></p> <p>Tina Rendon</p>
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Examiner:

In response to the Office Action dated September 20, 2000, please consider the following remarks.

REMARKS

Claims 1 - 30 and 36 - 45 are still pending in this application and have been rejected by Examiner.

1. The Office Action rejected Claims 1, 12 - 23, 26 - 30, 37, 38 and 40 under 35 U.S.C. § 103 as being unpatentable over the Hori patent (Hori '766), in view of the Hsieh *et al.* patent (Hsieh '035). Applicants respectfully traverse examiner's interpretation of the prior art as rendering the invention obvious over this patent. The Office Action notes that Hori '766 teaches how to form a FET with a silicon oxynitride gate dielectric. The Office Action also notes that Hsieh '035 teach how to use metal silicates as high permittivity capacitor dielectrics that minimize leakage currents. The Office Action then alleges it would be obvious to combine Hori '766's method of forming improved-mobility FETs having an oxynitride film with Hsieh '035's capacitor dielectric—and that this combination would form applicants' invention.